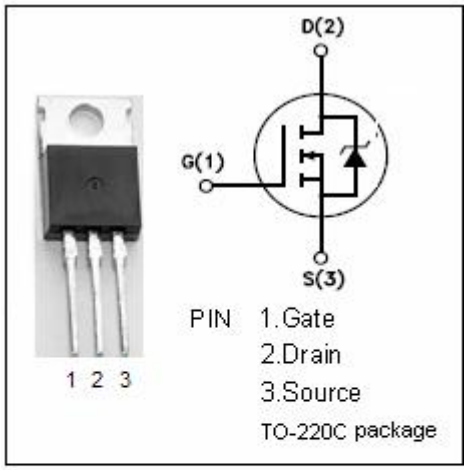
isc N-Channel MOSFET Transistor 8N05

• **DESCRIPTION**
• Drain Current I_D= 8A@ T_C=25℃
• Drain Source Voltage-
: V_{DSS}= 50V(Min)
• Fast Switching Speed



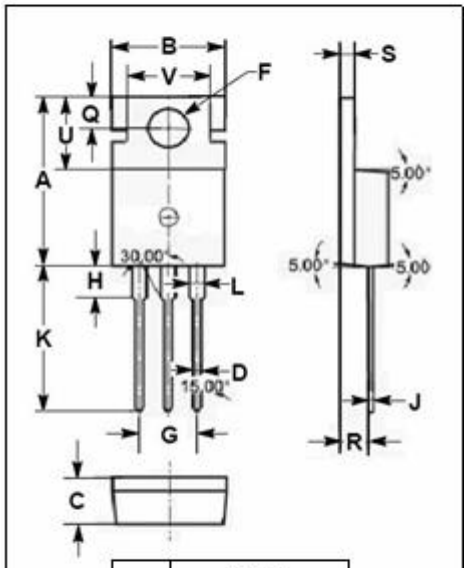
• **APPLICATIONS**
• General purpose power amplifier

• **ABSOLUTE MAXIMUM RATINGS(T_C=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	50	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ T_C=25℃	8	A
$I_{D(puls)}$	Pulse Drain Current	32	A
P_{tot}	Total Dissipation@T_C=25℃	125	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

• **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.25	℃/W



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D=250μA	50			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=250μA	2.0		4.0	V
V_{SD}	Diode Forward On-Voltage	I_S=8A ;V_{GS}= 0			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=4A			0.8	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 50V; V_{GS}= 0			20	μA